Silicon N-Channel Power MOSFET ®

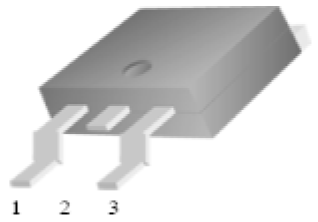
CS50N12 A4

General Description:

CS50N12 A4, the silicon N-channel Enhanced VDMOSFETs, is obtained by advanced Trench Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-252, which accords with the RoHS standard.

V_{DSS}	120	V
I_D	50	A
$P_D(T_C$=25℃)	83	W
$R_{DS(ON)Typ}$	15	mΩ

TO-252

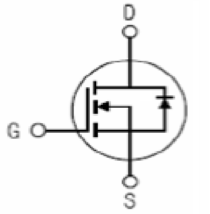


1.Gate 2.Drain 3.Source

Features:

- **Fast Switching**
- **Low ON Resistance**(Rdson≤20mΩ)
- **Low Gate Charge**
- **Low Reverse transfer capacitances**(Typical:112.9pF)
- **100% Single Pulse avalanche energy Test**

Inner Equivalent Principium Chart



Applications:

Power switch circuit of adaptor and charger.

Absolute （T_J= 25℃ unless otherwise specified）:

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	120	V
I_D	Continuous Drain Current T_C = 25 ℃	50	A
	Continuous Drain Current T_C = 100 ℃	31	A
$I_{DM}{}^{a1}$	Pulsed Drain Current T_C = 25 ℃	200	A
V_{GS}	Gate-to-Source Voltage	±20	V
$E_{AS}{}^{a2}$	Single Pulse Avalanche Energy	397.8	mJ
P_D	Power Dissipation T_C = 25 ℃	83	W
	Derating Factor above 25℃	0.666	W/℃
T_J， T_{stg}	Operating Junction and Storage Temperature Range	150， –55 to 150	℃

Electrical Characteristics（T_J= 25℃ unless otherwise specified）:

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250 μA	120	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS} =120V, V_{GS}= 0V, T_J = 25℃	--	--	1	μA
		V_{DS} =96V, V_{GS}= 0V, T_J = 125℃	--	--	100	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+20V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-20V	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=25A	--	15	20	mΩ
		V_{GS}=4.5V,I_D=15A		15.5	23	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.0	--	2.5	V

Pulse width tp≤300 μs, δ ≤2%

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	--	1.2	--	Ω
C_{iss}	Input Capacitance	V_{GS}=0V，V_{DS}=60V f=1.0MHz	--	4281	--	pF
C_{oss}	Output Capacitance		--	188.2	--	
C_{rss}	Reverse Transfer Capacitance		--	112.9	--	

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	V_{GS}=10V，R_G=4.7Ω V_{DD}=60V，I_D=30A	--	20.46	--	ns
tr	Rise Time		--	15	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	96.88	--	
t_f	Fall Time		--	105.46	--	
Q_g	Total Gate Charge	V_{GS}=10V，V_{DD}=96V I_D=30A	--	96.8	--	nC
Q_{gs}	Gate to Source Charge		--	10.2	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	25.7	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	T_C = 25 ℃	--	--	50	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	200	A
V_{SD}	Diode Forward Voltage	I_S=25A,V_{GS}=0V	--	--	1.2	V
trr	Reverse Recovery Time	I_S=30A,T_j = 25℃ dI_F/dt=100A/us,	--	54	--	ns
Qrr	Reverse Recovery Charge		--	97.74	--	nC
I_{RRM}	Reverse Recovery Current		--	3.62	--	A

Pulse width tp≤300 μs, δ ≤2%

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	1.5	℃/W
$R_{\theta JA}$	Junction-to-Ambient	100	℃/W

[a1]: Calculated continuous current based on maximum allowable junction temperature. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.

[a2]: L=0.5mH, I_D=39.89A, Start T_J=25℃

[a3]: Recommend soldering temperature defined by IPC/JEDEC J-STD 020

Characteristics Curve:

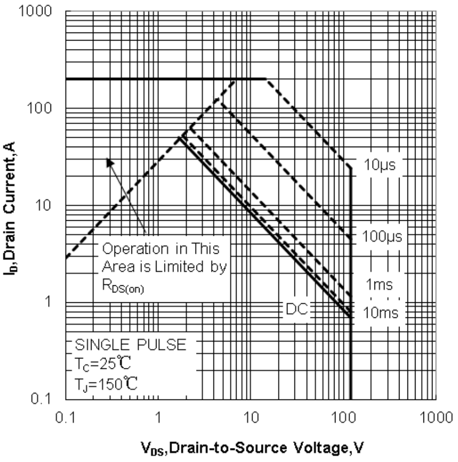


Figure1. Maximum Forward Bias Safe Operating Area

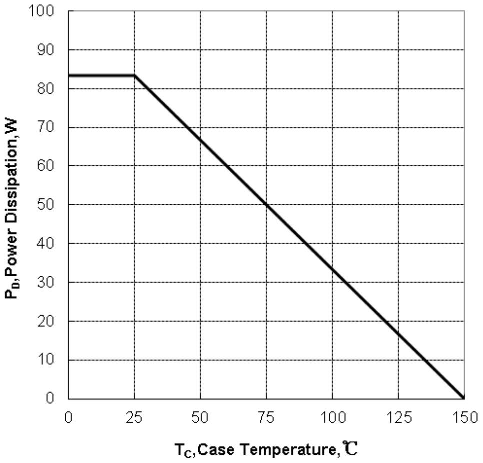


Figure2. Maximum Power Dissipation vs Case Temperature

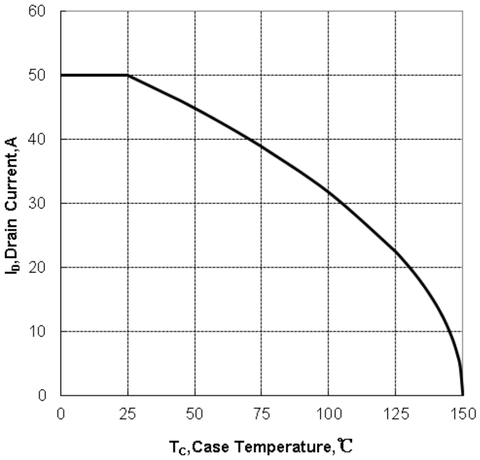


Figure3. Maximum Continuous Drain Current vs Case Temperature

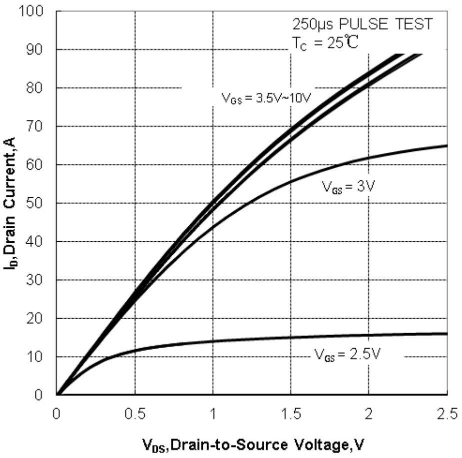


Figure 4. Typical Output Characteristics

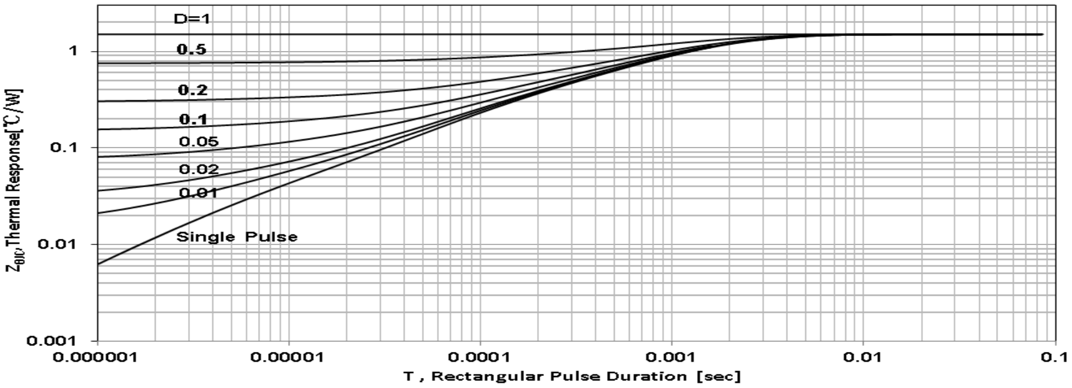


Figure5. Maximum Effective Transient Thermal Impedance, Junction-to-Case

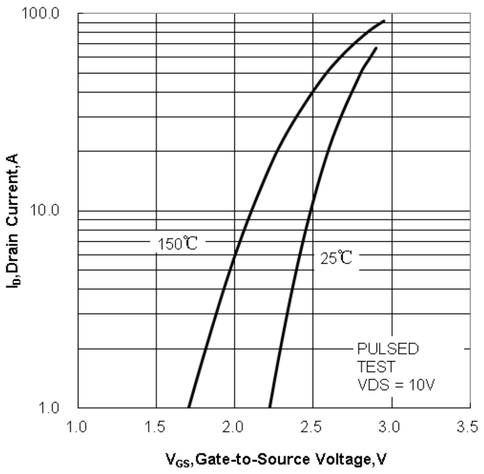


Figure 6. Typical Transfer Characteristics

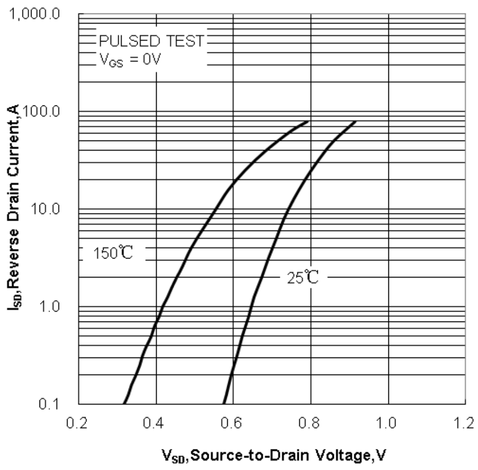


Figure 7. Typical Body Diode Transfer Characteristics

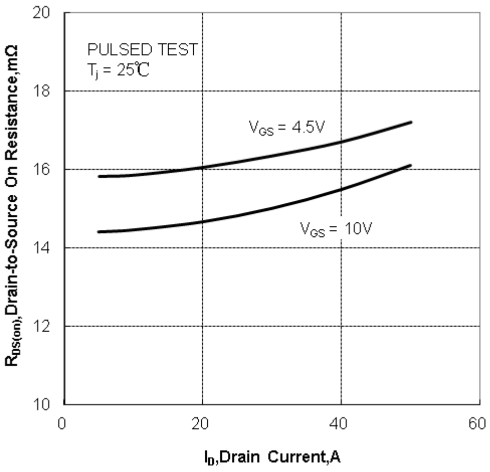


Figure 8. Drain-to-Source On Resistance vs Drain Current

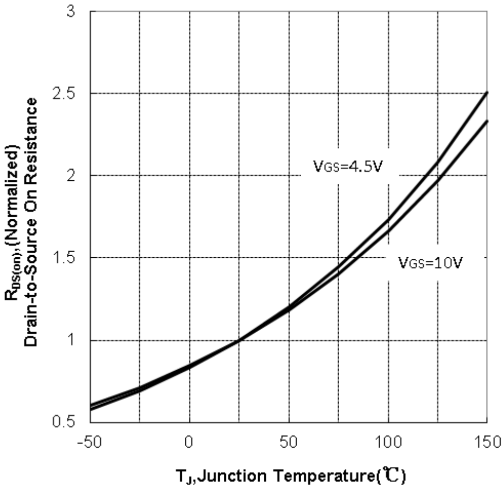


Figure 9. Nomalized on Resistance vs Junction Temperature

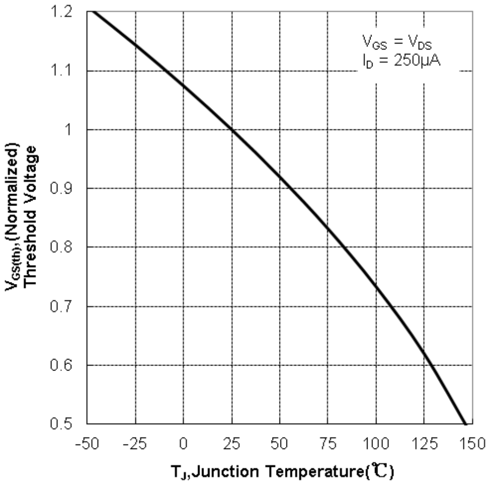


Figure 10. Nomalized Theshold Voltage vs Junction Temperature

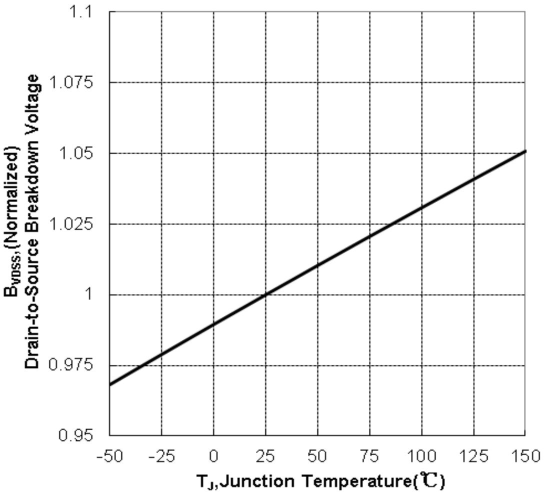


Figure 11. Nomalized Breakdown Voltage vs Junction Temperature

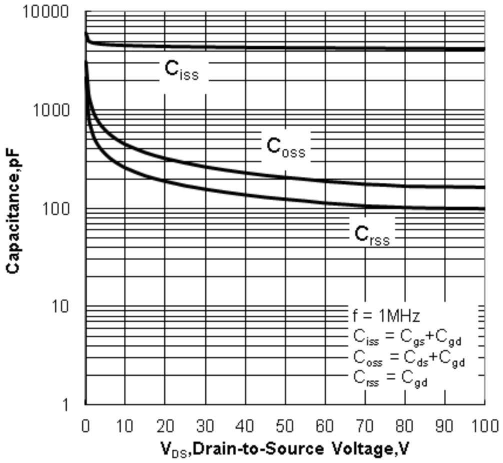


Figure12. Capacitance Characteristics

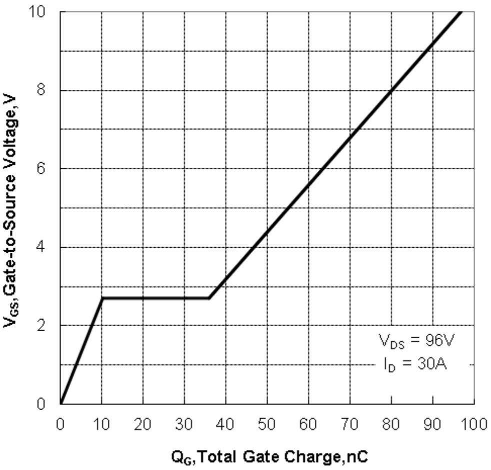


Figure13. Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform

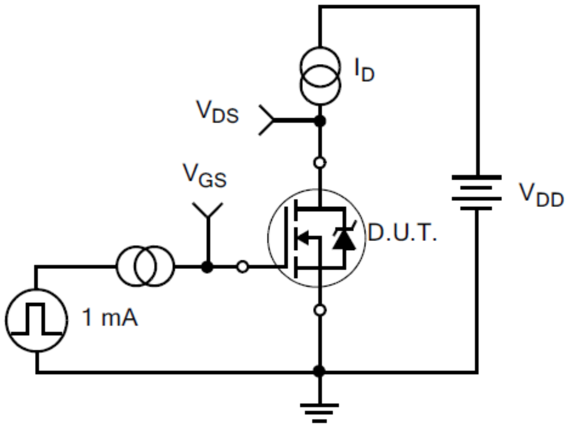


Figure 14. Gate Charge Test Circuit

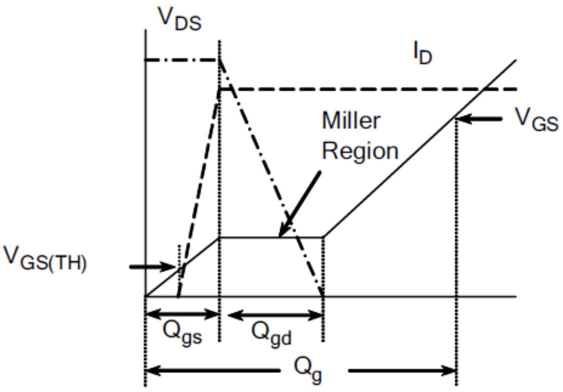


Figure 15. Gate Charge Waveforms

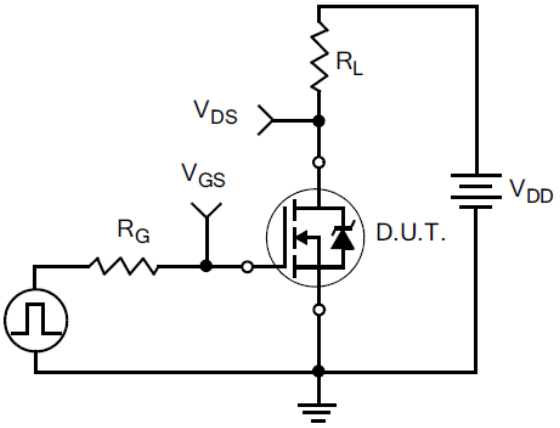


Figure 16. Resistive Switching Test Circuit

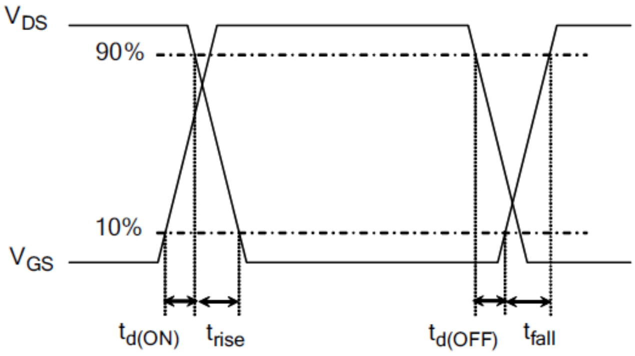


Figure 17. Resistive Switching Waveforms

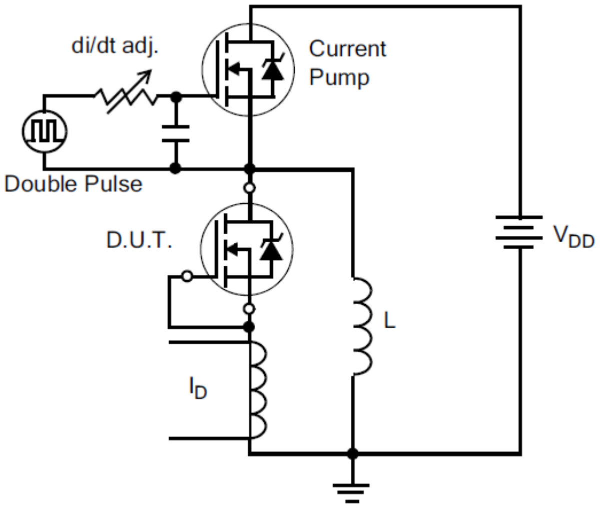


Figure 18. Diode Reverse Recovery Test Circuit

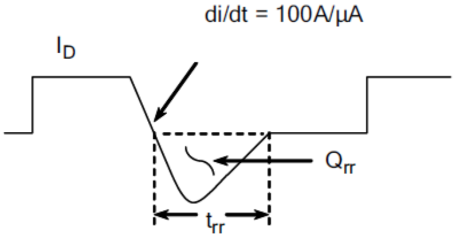


Figure 19. Diode Reverse Recovery Waveform

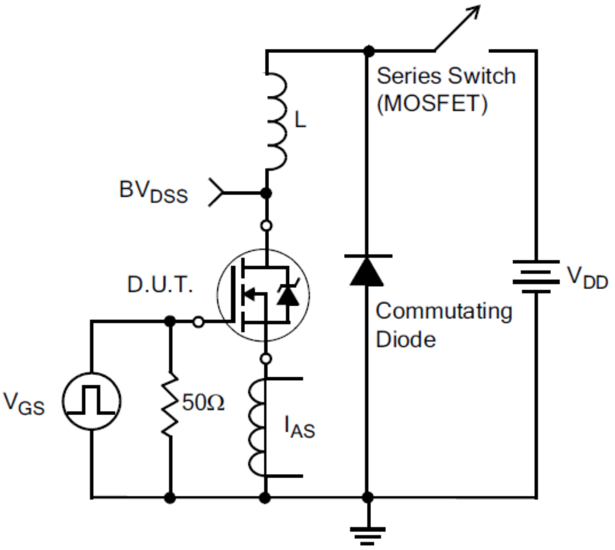
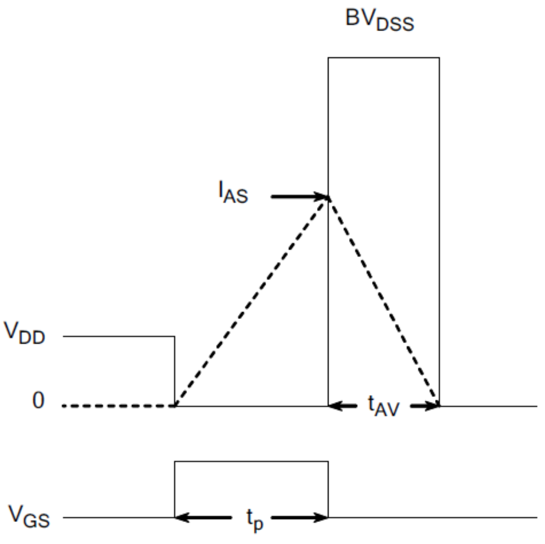


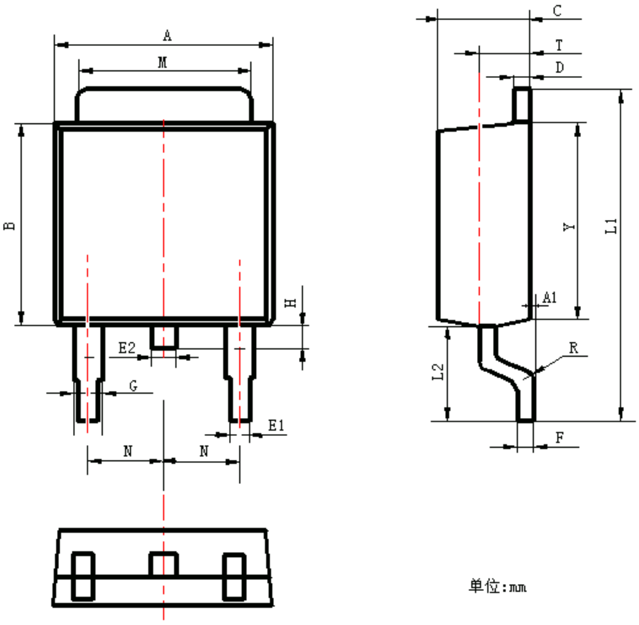
Figure 20. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^{2} L}{2}$$

Figure 21. Unclamped Inductive Switching Waveform

Package Information:



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
A1	0	0.16
B	5.70	6.30
C	2.10	2.50
D	0.30	0.70
E1	0.60	0.90
E2	0.70	1.00
F	0.30	0.60
G	0.70	1.20
L1	9.60	10.50
L2	2.70	3.10
H	0.40	1.00
M	5.10	5.50
N	2.09	2.49
R	0.3	
T	1.40	1.60
Y	5.10	6.30

TO-252 Package

The name and content of poisonous and harmful material in products

	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
Limit	≤0.1%	≤0.1%	≤ 0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○：Means the hazardous material is under the criterion of 2011/65/EU. ×：Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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